

ABSTRACT OF THE DISCLOSURE

Described herein is a method for soft-programming an electrically erasable nonvolatile memory device, wherein soft-programming is carried out with a soft-programming multiplicity equal to twice that used for writing data in the memory device until the current absorbed during soft-programming is smaller than or equal to the maximum current which is available for writing operations and which can be generated within the memory device, and with a soft-programming multiplicity equal to the one used for writing data in the memory device in the case where the current absorbed during soft-programming with double multiplicity is greater than the maximum current which is available for writing operations and which can be generated within the memory device.

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